Analog Power AM2321PE

P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

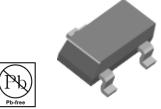
•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

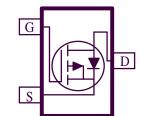
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology ESD

Protected COMPLIANT HALOGEN

FREE

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(OHM)$ $I_{D}(A)$		
-20	$0.079 @ V_{GS} = -4.5V$	-4.1	
	$0.110 @ V_{GS} = -2.5V$	-3.2	





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current ^a	T _A =25°C	.T_	-4.1		
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ър	-3.3	A	
Pulsed Drain Current ^b	·	I_{DM}	-10		
Continuous Source Current (Diode Conduction) ^a		I_S	±0.46	A	
D	$T_A=25^{\circ}C$	D_	1.25	w	
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	FD	0.8	• • • • • • • • • • • • • • • • • • • •	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
M · I · · · · · · · · · · · · · · · · ·	$t \le 5 \sec$	D	100	0000	
Maximum Junction-to-Ambient ^a	Steady-State	$\mathbf{K}_{\mathrm{THJA}}$	150	°C/W	

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Cymbol	Test Conditions	Limits			Unit
i arameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
Zero Gate Voltage Diani Current	DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	μΑ
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -1 \text{ V}$	-5			A
Drain-Source On-Resistance ^A		$V_{GS} = -4.5 \text{ V}, I_{D} = -1 \text{ A}$			79	mΩ
Diani-Source On-Resistance	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1 \text{ A}$			110	
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -1 \text{ A}$		9		S
Diode Forward Voltage	V_{SD}	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.65		V
Pulsed Body-Diode Current ^C	I_{SM}				-10	A
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		7.2		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -1 \text{ A}$		1.7		nC
Gate-Drain Charge	Q_{gd}	ID1 A		1.5		
Turn-On Delay Time	$t_{d(on)}$			10		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, I_{L} = -1 \text{ A},$		9		ns
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = -4.5 V, R_G = 6 Ω		27		118
Fall-Time	t _f			11		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

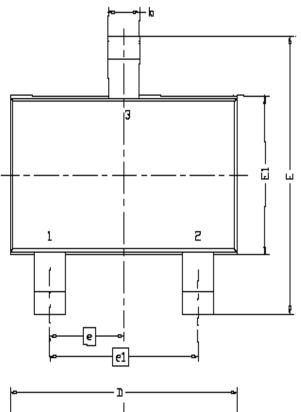
b. Guaranteed by design, not subject to production testing.

c. Repetitive rating, pulse width limited by junction temperature.

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Package Information

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DIM.	MILLIMETERS			
יוגודת	MIN	NDM	MAX	
Α	0.935	0.95	1.10	
A1	0.01		0.10	
A2	0.85	0.90	0.925	
Ь	0.30	0.40	0.50	
С	0.10	0.15	0,25	
D	2.70	2.90	3.10	
Ε	2.60	2.80	3.00	
E1	1.40	1.60	1.80	
6	0.95 BSC			
el	1.90 BSC			
L	0.30	0.40	0.60	
L1	0.60REF			
L2	0,25BSC			
R	0.10			
θ	Û.	4*	8,	
81	7*N□M			

